

## High-speed double diode

1PS300

## FEATURES

- Very small plastic SMD package
- High switching speed: max. 4 ns
- Continuous reverse voltage: max. 80 V
- Repetitive peak reverse voltage: max. 85 V
- Repetitive peak forward current: max. 500 mA.

## APPLICATIONS

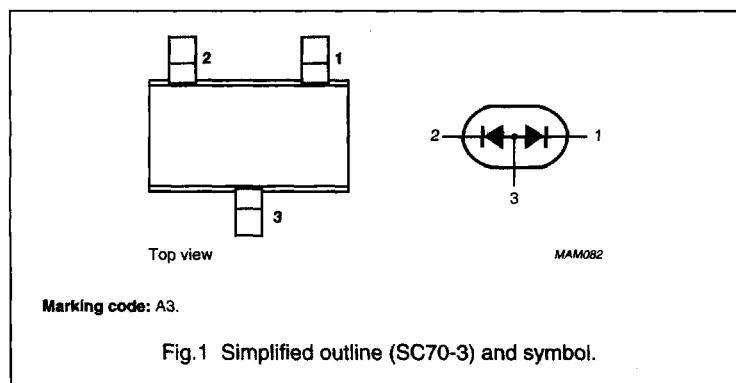
- High-speed switching in e.g. surface mounted circuits.

## DESCRIPTION

The 1PS300 consists of two high-speed switching diodes with common anodes, fabricated in planar technology, and encapsulated in the very small rectangular plastic SMD SC70-3 package.

## PINNING

PIN	DESCRIPTION
1	cathode (k1)
2	cathode (k2)
3	common anode



## LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
<b>Per diode</b>					
$V_{RRM}$	repetitive peak reverse voltage		–	85	V
$V_R$	continuous reverse voltage		–	80	V
$I_F$	continuous forward current	single diode loaded; see Fig.2; note 1	–	200	mA
		double diode loaded; see Fig.2; note 1	–	170	mA
$I_{FRM}$	repetitive peak forward current		–	500	mA
$I_{FSM}$	non-repetitive peak forward current	square wave; $T_j = 25\text{ °C}$ prior to surge			
		$t = 1\ \mu\text{s}$	–	4	A
		$t = 1\ \text{s}$	–	0.5	A
$P_{tot}$	total power dissipation	$T_{amb} = 25\text{ °C}$ ; note 1	–	300	mW
$T_{stg}$	storage temperature		–65	+150	°C
$T_j$	junction temperature		–	150	°C

## Note

1. Device mounted on an FR4 printed-circuit board.

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**ELECTRICAL CHARACTERISTICS** $T_j = 25\text{ }^\circ\text{C}$ ; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
<b>Per diode</b>					
$V_F$	forward voltage	see Fig.3			
		$I_F = 1\text{ mA}$	610	–	mV
		$I_F = 10\text{ mA}$	740	–	mV
		$I_F = 50\text{ mA}$	–	1.0	V
		$I_F = 100\text{ mA}$	–	1.2	V
$I_R$	reverse current	see Fig.4			
		$V_R = 25\text{ V}$	–	30	nA
		$V_R = 80\text{ V}$	–	0.5	$\mu\text{A}$
		$V_R = 25\text{ V}; T_j = 150\text{ }^\circ\text{C}$	–	30	$\mu\text{A}$
		$V_R = 80\text{ V}; T_j = 150\text{ }^\circ\text{C}$	–	100	$\mu\text{A}$
$C_d$	diode capacitance	$f = 1\text{ MHz}; V_R = 0$ ; see Fig.5	–	2	pF
$t_{rr}$	reverse recovery time	when switched from $I_F = 10\text{ mA}$ to $I_R = 10\text{ mA}; R_L = 100\ \Omega$ ; measured at $I_R = 1\text{ mA}$ ; see Fig.6	–	4	ns
$V_{fr}$	forward recovery voltage	when switched from $I_F = 10\text{ mA}$ ; $t_r = 20\text{ ns}$ ; see Fig.7	–	1.75	V

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-tp}$	thermal resistance from junction to tie-point		200	K/W
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	415	K/W

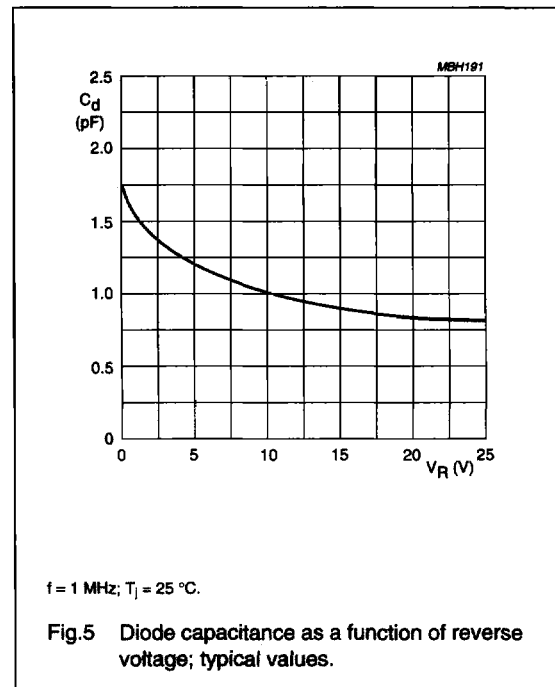
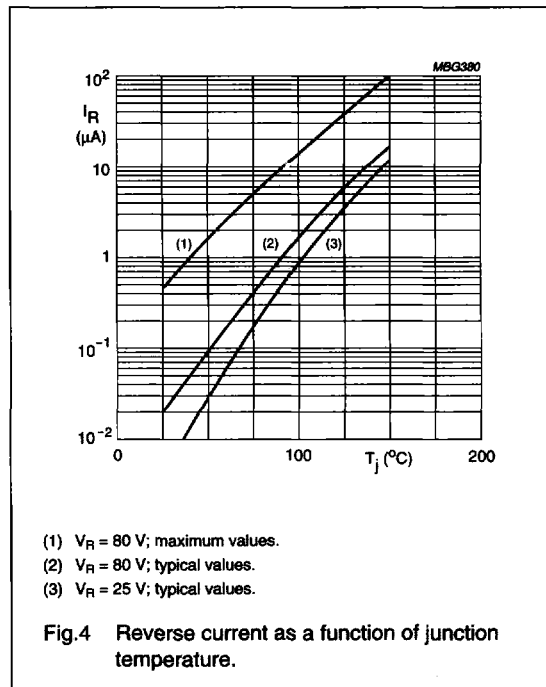
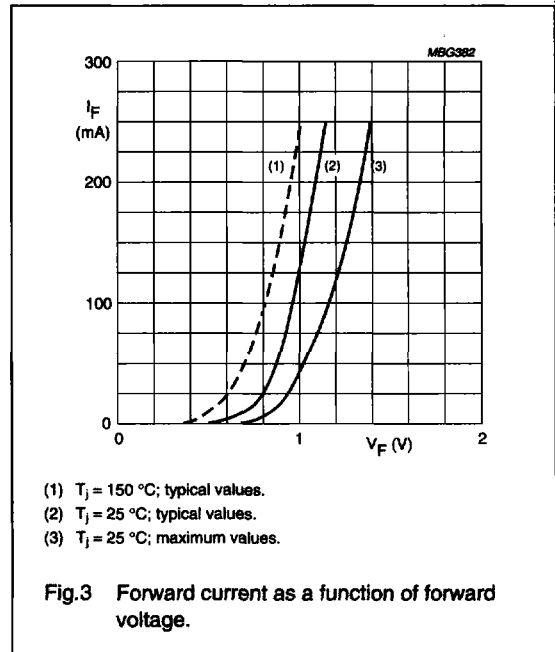
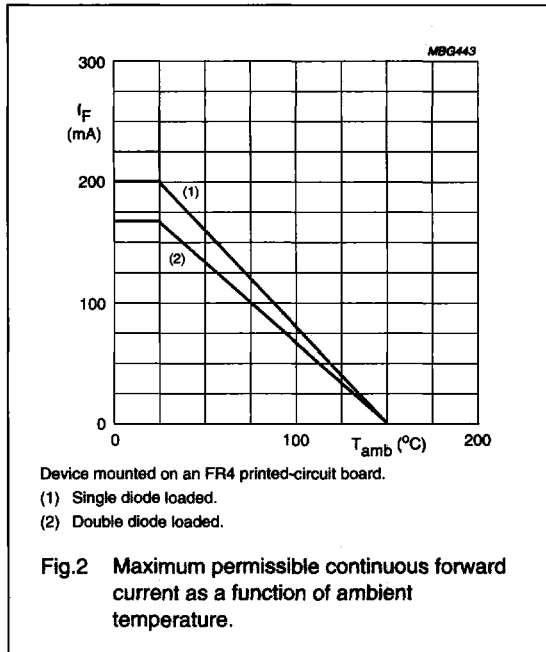
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## GRAPHICAL DATA



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